N-Channel 150-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

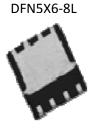
Typical Applications:

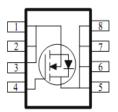
- PoE PSE and PD Circuits
- · LED Inverter Circuits
- 48V-Input DC/DC Conversion Circuits

PRODUCT SUMMARY					
V _{DS} (V)	$V_{DS}(V)$ $r_{DS(on)}(m\Omega)$				
150	62 @ V _{GS} = 10V	7.4			
	80 @ V _{GS} = 6.5V	6.5			



ROHS
COMPLIANT
HALOGEN
FREE





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Parameter				Limit	Units		
Drain-Source Voltage			V_{DS}	150	V		
Gate-Source Voltage			V_{GS}	±20	V		
Continuous Drain Courset a		T _A =25°C	ı	7.4			
Continuous Drain Current ^a		T _A =70°C	l _D	5.9	Α		
Pulsed Drain Current ^b				30			
Continuous Source Current (Diode Conduction) a	Is	6.6	Α				
Davier Dissipation 8		$T_A=25$ °C $T_A=70$ °C	P_{D}	5	W		
Power Dissipation ^a			гD	3.2	v v		
Operating Junction and Storage Temperature Range				-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State	IΛθJA	65	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

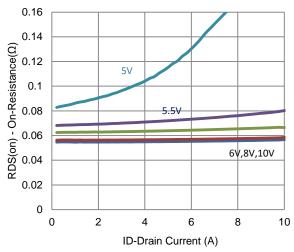
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zara Cata Valtaga Drain Current	1	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 120 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	10		10	T UA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	11			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, I_D = 3.7 \text{ A}$			62	mΩ	
	r _{DS(on)}	$V_{GS} = 6.5 \text{ V}, I_D = 3.2 \text{ A}$			80	11177	
Forward Transconductance a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 3.7 \text{ A}$		13		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 3.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.75		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 75 \text{ V}, V_{GS} = 6.5 \text{ V},$		15		nC	
Gate-Source Charge	Q_{gs}	$I_{DS} = 73 \text{ V}, \text{ V}_{GS} = 0.3 \text{ V},$ $I_{D} = 3.7 \text{ A}$		3.4			
Gate-Drain Charge	Q_gd	1B = 3.7 A		7.6			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 75 \text{ V}, R_{L} = 20.3 \Omega,$		8			
Rise Time	t _r	$V_{DS} = 75 \text{ V}, K_L - 20.3 \Omega,$ $I_D = 3.7 \text{ A},$		12		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		30		ns	
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.12		16			
Input Capacitance	C _{iss}			968			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		139		pF	
Reverse Transfer Capacitance	C _{rss}			85			

Notes

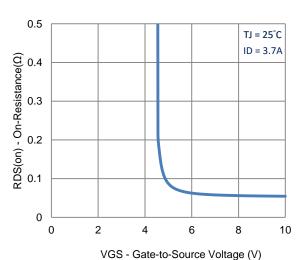
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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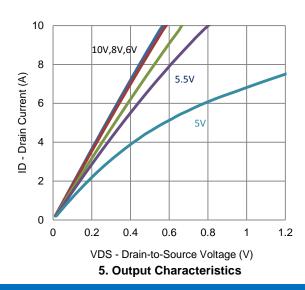
Typical Electrical Characteristics



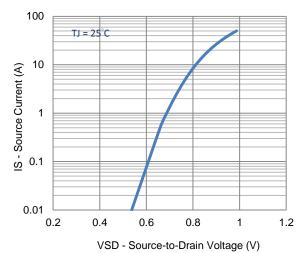
1. On-Resistance vs. Drain Current



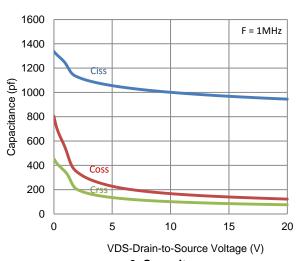
3. On-Resistance vs. Gate-to-Source Voltage



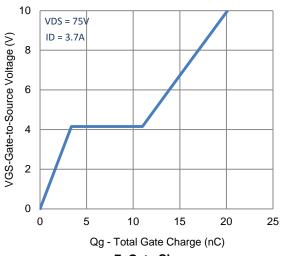
2. Transfer Characteristics



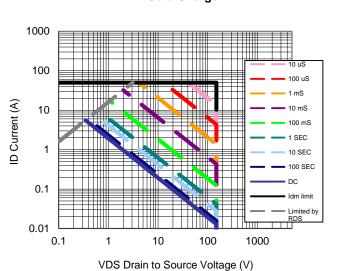
4. Drain-to-Source Forward Voltage



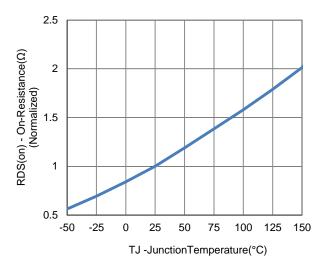
Typical Electrical Characteristics



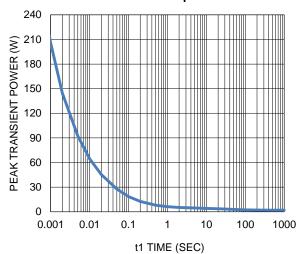
7. Gate Charge



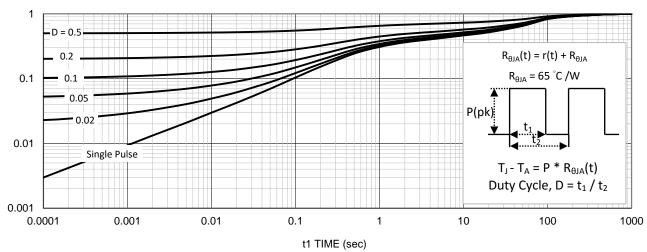
9. Safe Operating Area



8. Normalized On-Resistance Vs Junction Temperature

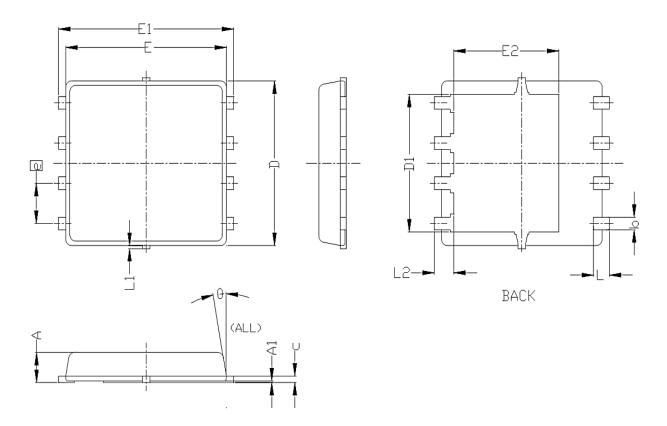


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
STMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0.95	1.00	0.033	0.037	0. 039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
Е		5. 55 BSC			0.219 BSC		
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	